

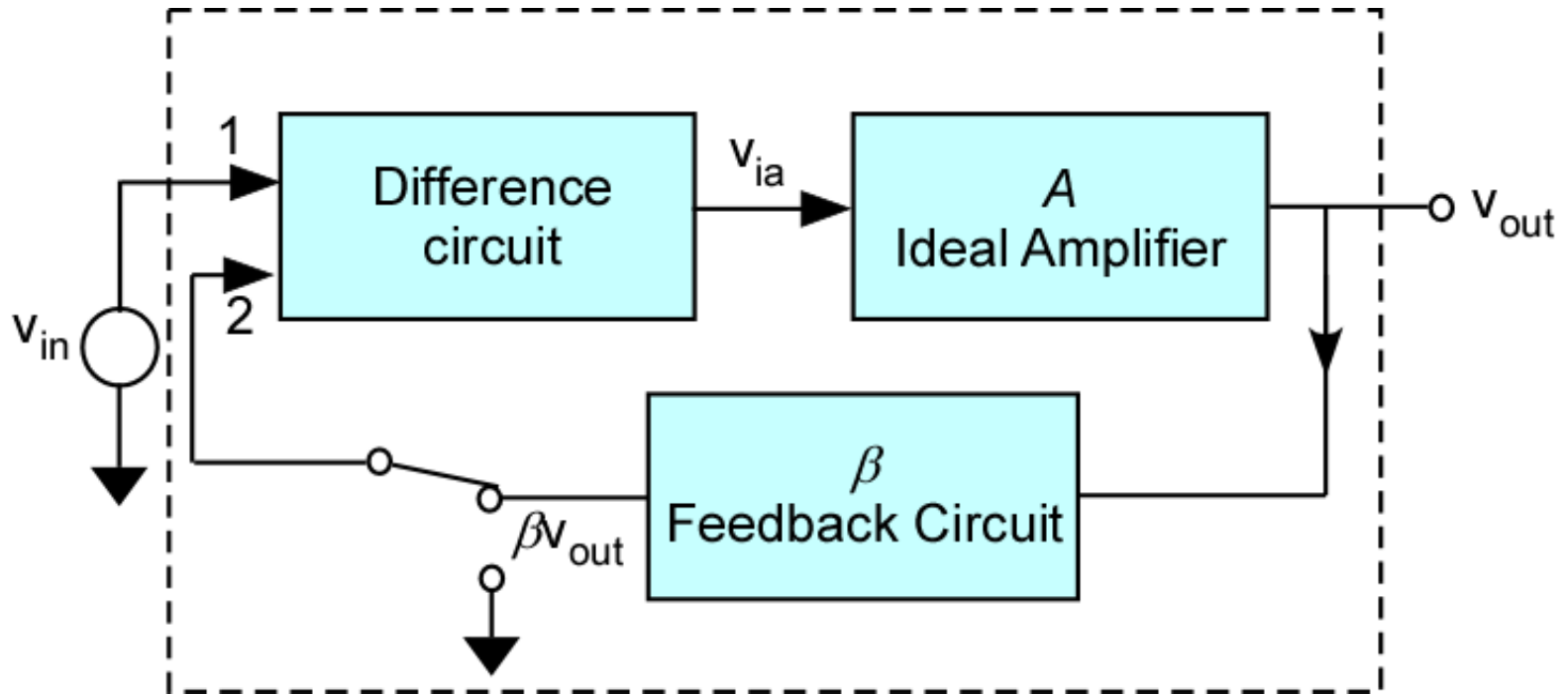
ECE 453

Wireless Communication Systems

Oscillators

Jose E. Schutt-Aine
Electrical & Computer Engineering
University of Illinois
jesa@Illinois.edu

Feedback – Basic Concept



Feedback and Frequency Dependence

1. The closed-loop transfer function is a function of frequency
2. The manner in which the loop gain varies with frequency determines the stability or instability of the feedback amplifier
3. The frequency at which the phase of the transfer function is equal to 180° will be unstable if the magnitude is greater than unity

Feedback and Stability

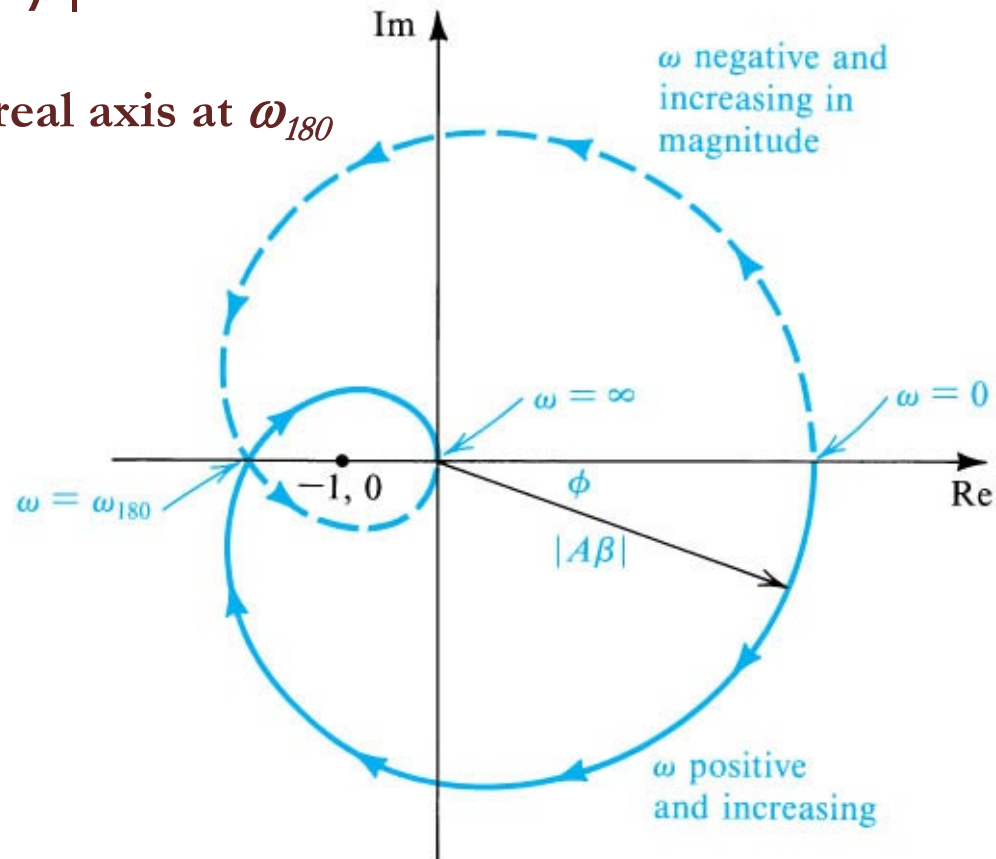
$$A_f(s) = \frac{A(s)}{1 + A(s)\beta(s)}$$

$$A_f(j\omega) = \frac{A(j\omega)}{1 + A(j\omega)\beta(j\omega)}$$

When loop gain $A(j\omega)\beta(j\omega)$ has 180° phase, we have positive feedback

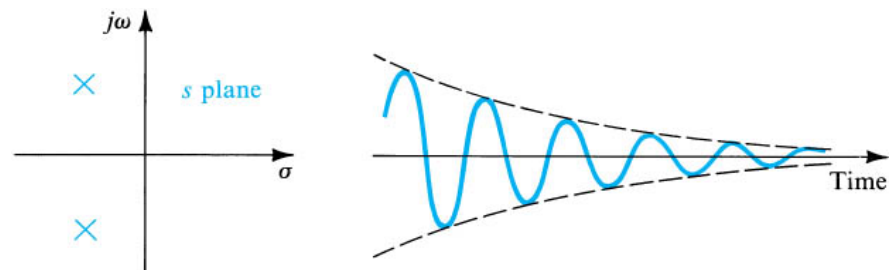
Nyquist Plot

- Radial distance is $|A\beta|$
- Angle is phase of ϕ
- Intersects negative real axis at ω_{180}

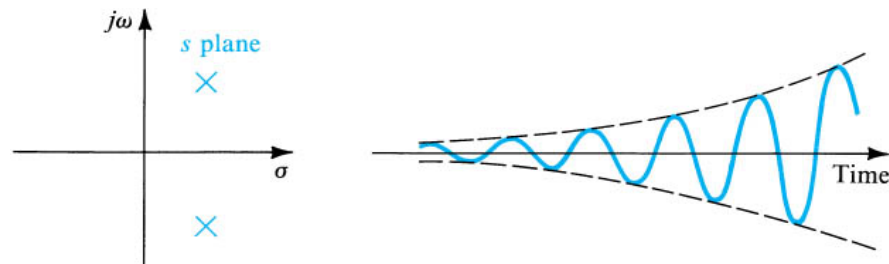


Stability and Pole Location

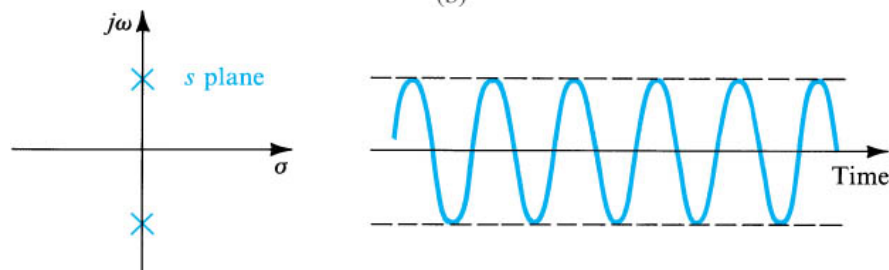
$$v(t) = e^{\sigma_o t} \left[e^{+j\omega t} + e^{-j\omega t} \right] = 2e^{\sigma_o t} \cos(\omega_n t)$$



(a)

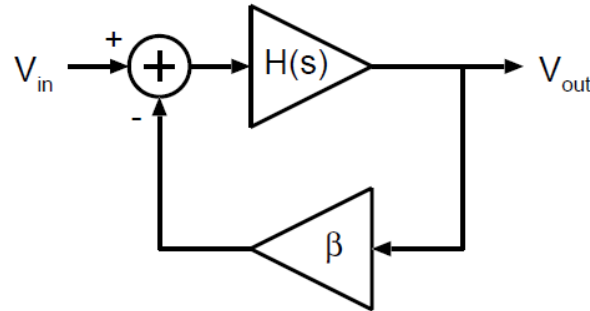


(b)



(c)

Oscillator



- Closed-Loop Transfer function:

$$-\frac{V_{out}}{V_{in}}(s) = \frac{H(s)}{1 + \beta H(s)}, \text{ where } s = j\omega$$

- Barkhausen's criteria for oscillation:

$$\rightarrow |\beta H(j\omega_0)| = 1$$

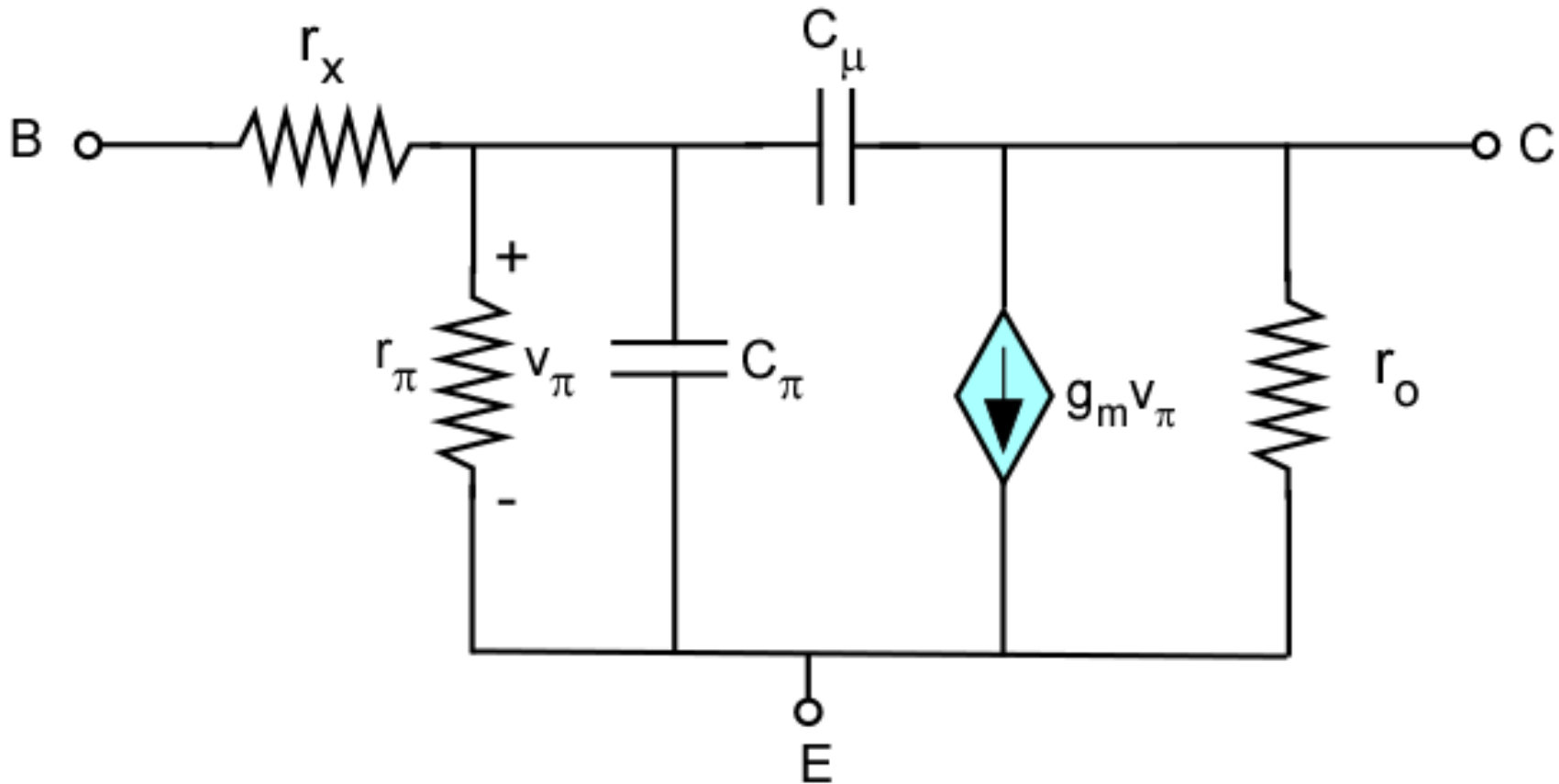
$$\rightarrow \arg(\beta H(j\omega_0)) = -180^\circ.$$

- ω_0 = oscillation-frequency.

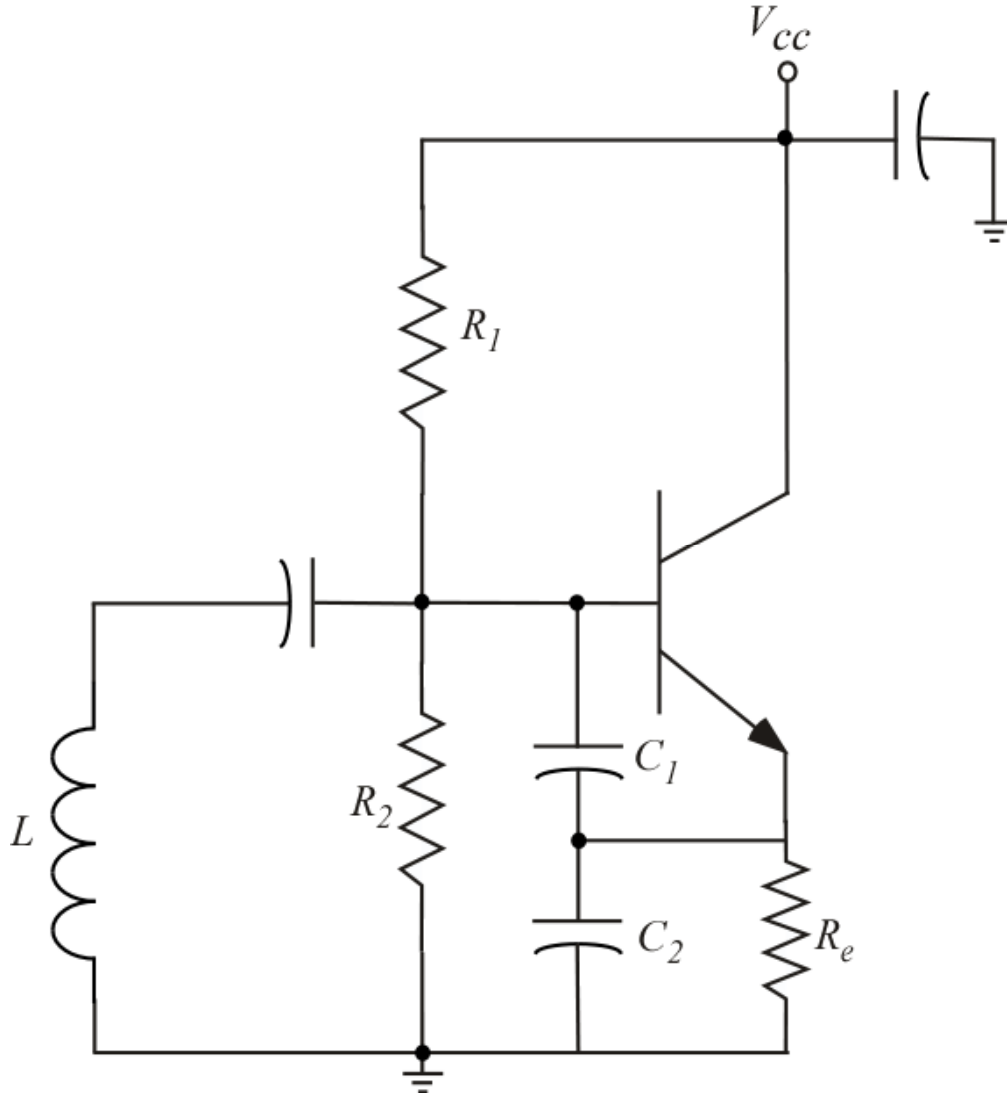
Oscillator Topologies

- **Common-base topology is usually preferred because**
 - Feedback within transistor is minimized (low Miller)
 - External feedback is dominant
 - Current gain has little phase shift and is constant with f
- **Oscillator built around 2 major requirements:**
 - Oscillation frequency f_o
 - Power P_o that must be delivered to a load
- **Other criteria**
 - Efficiency
 - Spectral purity
 - Frequency stability

BJT – High-Frequency Model



Common-Collector Colpitts



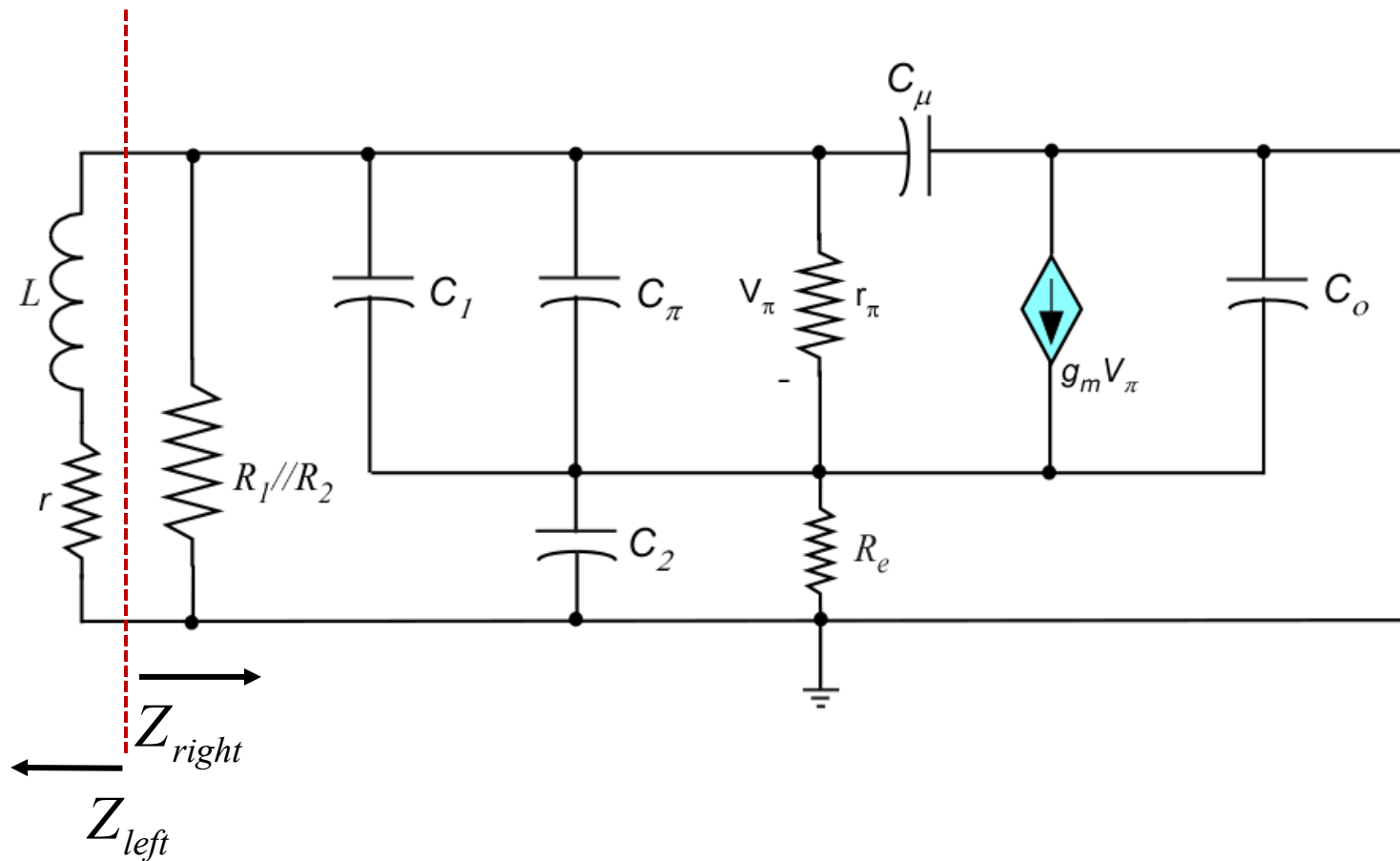
- Minimize circuit dependence on transistor internal parameters

- Choose

$$C_1 \gg C_\pi$$

$$C_2 \gg C_o$$

Incremental Model



For Oscillation, we want $Z_{left} = -Z_{right}$

Oscillation Criteria

Condition gives

$$\frac{1}{\omega^2 C_1^2 r_\pi} + \frac{1}{\omega^2 C_2^2 R_e} + r + g_m \left(\frac{1}{\omega^4 C_1^2 C_2^2 r_\pi R_e} - \frac{1}{\omega^2 C_1 C_2 R_e} \right) = 0$$

Term in ω^{-4} can be neglected. This gives

$$\frac{g_m}{\omega^2 C_1^2 \beta} + \frac{1}{\omega^2 C_2^2 R_e} + r - \frac{g_m}{\omega^2 C_1 C_2 R_e} = 0$$

Gives transconductance g_{ms} to set net resistance to zero

$$g_{ms} = \frac{\omega^2 C_1 C_2 r + \frac{C_1}{C_2 R_e}}{1 - \frac{C_2}{C_1 \beta}}$$

Oscillation Conditions

g_{ms} is the transconductance needed to support steady-state oscillations

If $g_m \ll \omega C_1 \beta$ and assuming that β is large,

$$g_{ms} \simeq \omega^2 C_1 C_2 r + \frac{C_1}{C_2} \frac{1}{R_e}$$

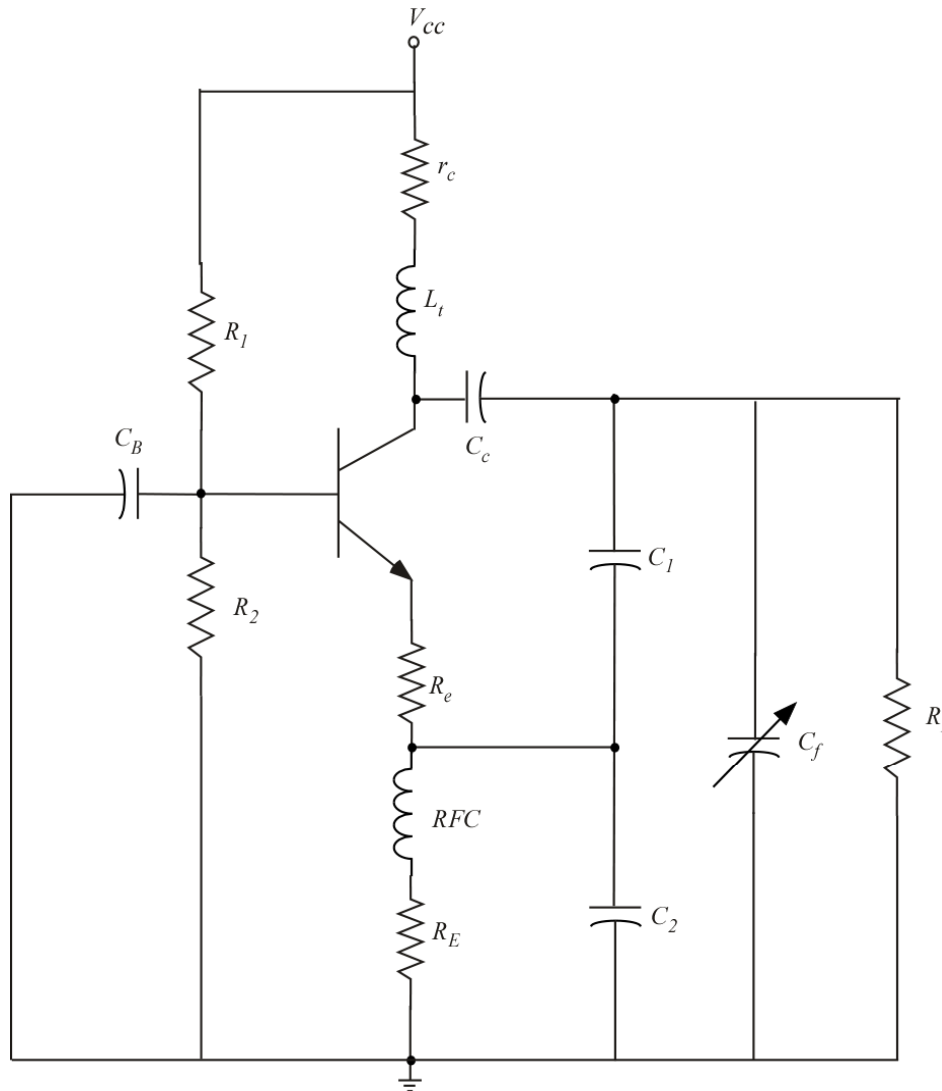
In terms of the inductor quality factor Q_L

$$g_{ms} \simeq \frac{\omega_o (C_1 + C_2)}{Q_L} + \frac{C_1}{C_2} \frac{1}{R_e}$$

CC-Colpitts - Observation

- **To implement tunable oscillator**
 - Use variable capacitor in parallel or in series with inductor
 - **To extract power from oscillator**
 - Place resistance in shunt with inductor
 - Account for loading effect in analysis and design
1. Oscillation amplitude builds up and v_{be} increases
 2. Transistor moves out of linear range and operation becomes nonlinear. Transconductance decreases.
 3. When transconductance reaches $g_{ms'}$ steady state operation is achieved.

Common-Base Colpitts



C_f : tuning capacitor

C_1 & C_2 : feedback ratio

RFC : RF choke to prevent power dissipation in R_E

R_p is equivalent resistance of coil L_t .

DEFINITIONS

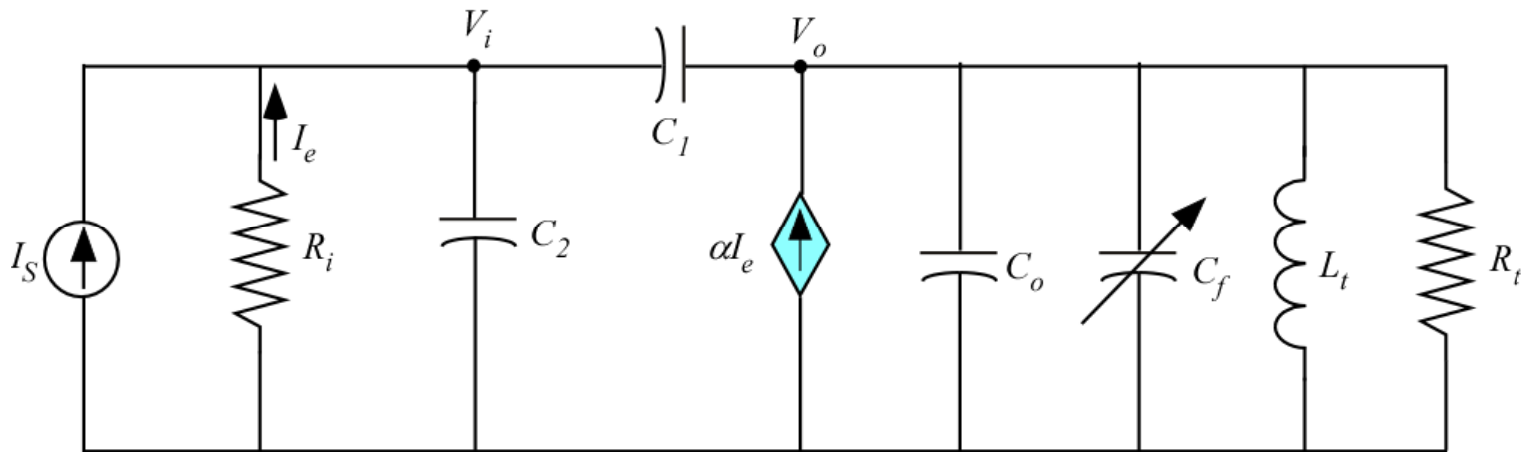
$$R_t = R_L \parallel R_p = \frac{R_L R_p}{R_L + R_p}$$

$$R_i = R_e + r_e$$

$$g_i = 1 / R_i$$

$$g_t = 1 / R_t$$

CB-Colpitts - Incremental Model



$$\begin{bmatrix} I_S \\ 0 \end{bmatrix} = \begin{bmatrix} g_i + s(C_1 + C_2) & -sC_1 \\ -\alpha g_i - sC_1 & g_t + s(C_1 + C_o + C_f) + \frac{1}{sL_t} \end{bmatrix} \begin{bmatrix} V_i \\ V_o \end{bmatrix}$$

Setting the determinant to zero provides the criterion for the onset of oscillation.

CB-Colpitts - Oscillation Conditions

Setting the determinant to zero gives.

$$\Delta(s) = g_i + s(L_t g_t g_i + C_a) + s^2(L_t g_i C_b + L_t g_t C_a - L_t C_1 \alpha g_i) + s^3(L_t C_a C_b - L_t C_1^2) = 0$$

Defining $C_a = C_1 + C_2$ **and** $C_b = C_1 + C_o + C_f$

we get a complex conjugate pair of roots. This leads to 2 equations for real and imaginary parts that must be equal to zero separately

$$\text{Re}[\Delta(j\omega)] = g_i - \omega^2 L_t (C_b g_i + C_a g_t - C_1 \alpha g_i) = 0$$

$$\text{Im}[\Delta(j\omega)] = L_t g_t g_i + C_a - \omega^2 L_t (C_a C_b - C_1^2) = 0$$

CB-Colpitts - Oscillation Conditions

From the equation for the imaginary part, we get

$$\omega_o^2 = \frac{g_t g_i + s(C_a / L_t)}{C_a C_b - C_t^2}$$

or

$$\omega_o^2 = \underbrace{\frac{1}{L_t \left[C_o + C_f + \left(C_1 C_2 / (C_1 + C_2) \right) \right]}}_{LC \text{ tank circuit}} + \underbrace{\frac{1}{R_t R_i \left[(C_f + C_o)(C_1 + C_2) + C_1 C_2 \right]}}_{\text{transistor and load}}$$

First term should predominate

CB-Colpitts - Oscillation Conditions

In that case

$$L_t \ll R_t R_i (C_1 + C_2)$$

which leads to
$$\omega_o^2 = \frac{1}{L_t \left[C_o + C_f + C_1 C_2 / (C_1 + C_2) \right]}$$

Circuit oscillates at frequency determined by L_t and equivalent capacitance.

CB-Colpitts - Oscillation Conditions

The solution of the real part using $\omega = \omega_o$ gives

$$\alpha_{\min} = 1 + \frac{C_f + C_o}{C_1} + \frac{R_i}{R_t} \left(1 + \frac{C_2}{C_1} \right) - \frac{1}{\omega_o^2 L_t C_1}$$

$$\alpha_{\min} \approx 1 - \frac{C_2}{C_1 + C_2} + \frac{R_i}{R_t} \left(1 + \frac{C_2}{C_1} \right) = \frac{1}{1 + (C_2 / C_1)} + \frac{R_i}{R_t} \left(1 + \frac{C_2}{C_1} \right)$$

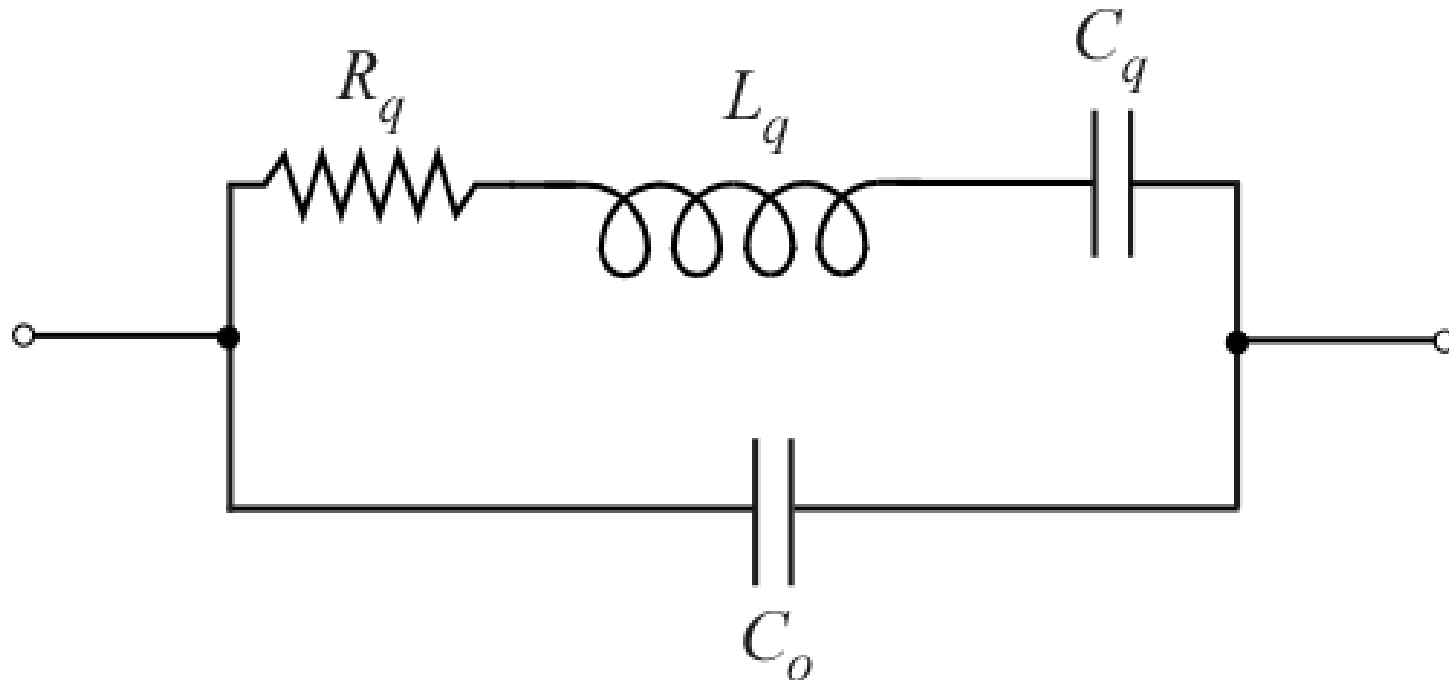
For oscillations to start, α of the transistor should be greater than $\alpha_{\min}$.

Crystal Oscillator

- **Quartz exhibits piezoelectric effect**
 - Reciprocal relationship between mechanical deformation and appearance of electrical potential
 - Deforming crystal produces voltage
 - Applying voltage produces deformation
- **When applied voltage is sinusoidal**
 - Mechanical oscillations that exhibit resonances at multiple frequencies
 - Extremely high Q that can reach 10^5 and 10^6
 - Do not work above 250 MHz

Crystal Resonator - Circuit Model

R_q , L_q and C_q describe mechanical resonance behavior
 C_o is capacitance due to external contacting



- L_q, C_q, R_q describe mechanical resonance
- C_o is due to external contacting

Crystal Resonance Frequencies

Admittance from terminals is

$$Y = j\omega C_0 + \frac{1}{R_q + j\left[\omega L_q - 1 / \left(\omega C_q\right)\right]} = G + jB$$

Resonance condition is expressed by

$$\omega_0 C_o - \frac{\omega_0 L_q - 1 / \left(\omega_0 C_q\right)}{R_q^2 + \left[\omega_0 L_q - 1 / \left(\omega_0 C_q\right)\right]^2} = 0$$

Crystal Resonance Frequencies

Series resonance frequency

$$\omega_0 = \omega_s \approx \omega_{s0} \left[1 + \frac{R_q^2}{2} \left(\frac{C_0}{L_q} \right) \right]$$

Parallel resonance frequency

$$\omega_0 = \omega_p \approx \omega_{p0} \left[1 - \frac{R_q^2}{2} \left(\frac{C_0}{L_q} \right) \right]$$

where

$$\omega_{s0} = 1 / \sqrt{L_q C_q} \qquad \omega_{p0} = \sqrt{(C_q + C_0) / (L_q C_q C_0)}$$

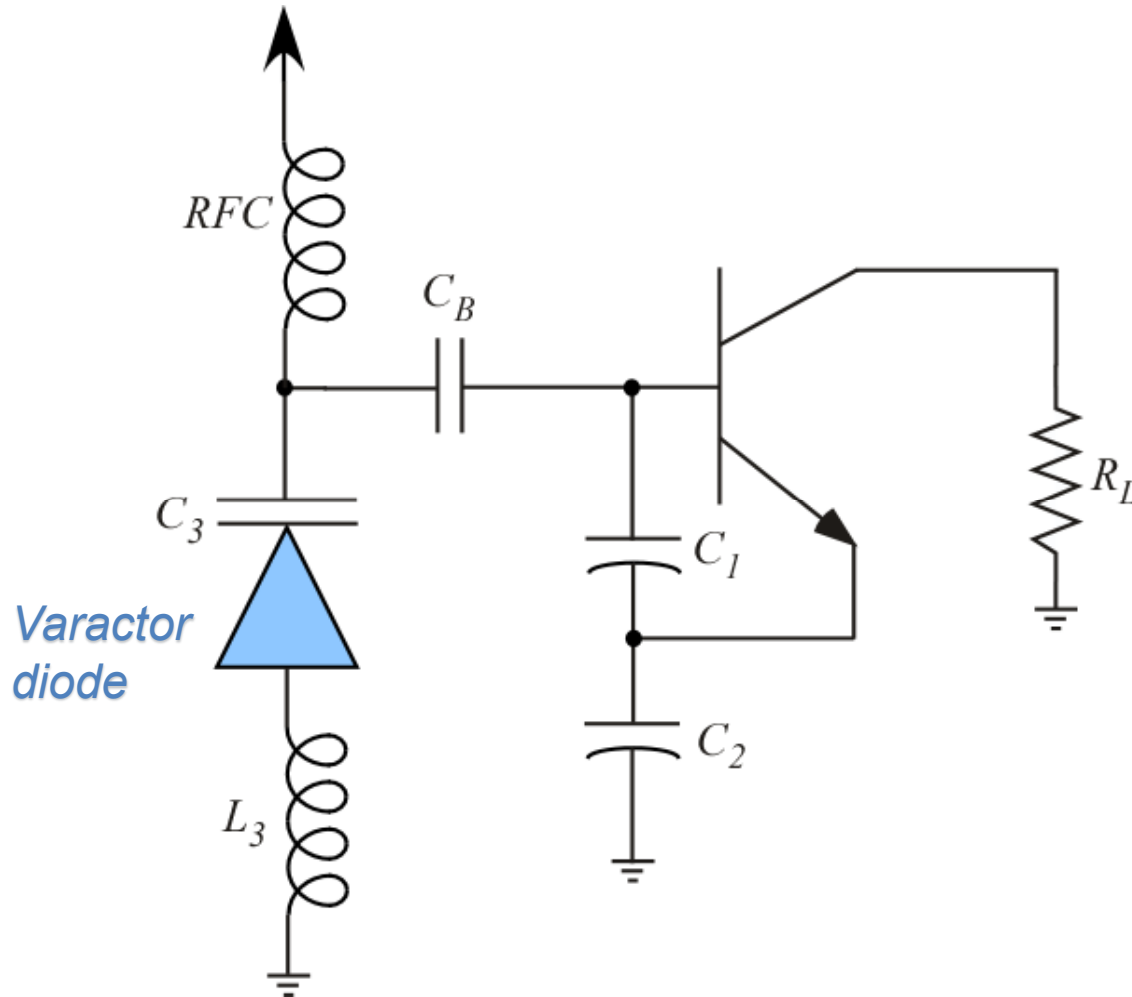
Crystal Oscillator - Example

Crystal is characterized by $L_q = 0.1\text{H}$, $R_q = 25\Omega$, $C_q = 0.3\text{pF}$, and $C_0 = 1\text{ pF}$. Find series and parallel resonance frequencies and compare them against the susceptance formula.

$$f_s = f_{s0} \left[1 + \frac{R_q^2}{2} \left(\frac{C_0}{L_q} \right) \right] = \frac{1}{2\pi \sqrt{L_q C_q}} \left[1 + \frac{R_q^2}{2} \left(\frac{C_0}{L_q} \right) \right] = 0.919 \text{ MHz}$$

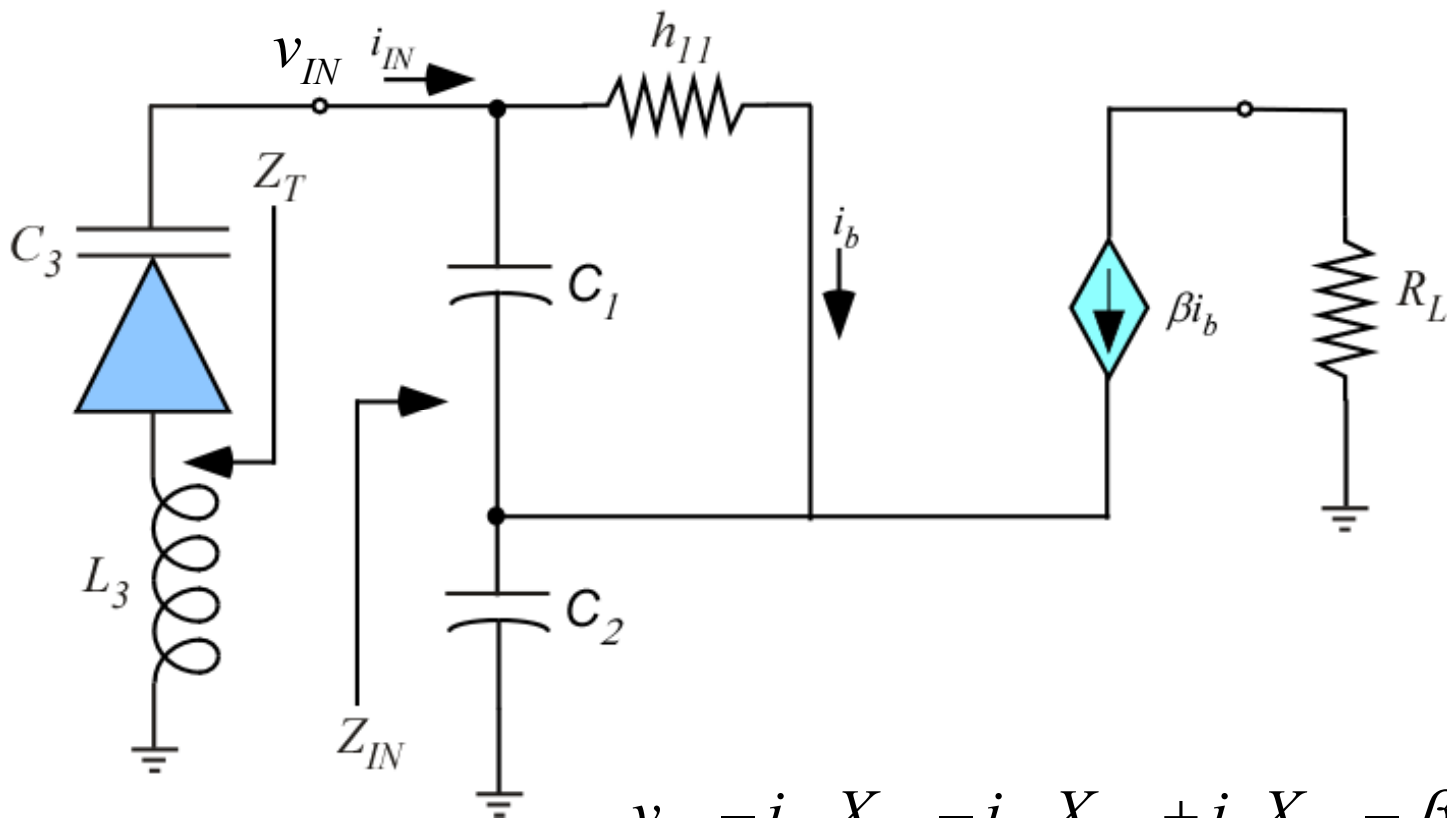
$$f_p = f_{p0} \left[1 - \frac{R_q^2}{2} \left(\frac{C_0}{L_q} \right) \right] = \frac{1}{2\pi \sqrt{\frac{C_q + C_0}{L_q C_q C_0}}} \left[1 - \frac{R_q^2}{2} \left(\frac{C_0}{L_q} \right) \right] = 1.048 \text{ MHz}$$

Voltage Controlled Oscillator



Varactor diode exhibits large change in capacitance in response to an applied bias voltage

Voltage Controlled Oscillator



$$v_{IN} - i_{IN}X_{C1} - i_{IN}X_{C2} + i_B X_{C1} - \beta i_B X_{C2} = 0$$

$$h_{11}i_B + i_B X_{C1} - i_{IN}X_{C1} = 0$$

Voltage Controlled Oscillator

Finding input impedance

$$Z_{IN} = \frac{1}{h_{11} + X_{C1}} \left[h_{11} (X_{C1} + X_{C2}) + X_{C1} X_{C2} (1 + \beta) \right]$$

Re-write as (assuming $h_{11} \gg X_{C1}$ and $\beta + 1 \sim \beta$)

$$Z_{IN} = \frac{1}{j\omega} \left[\frac{1}{C_1} + \frac{1}{C_2} \right] - \frac{\beta}{h_{11}} \left(\frac{1}{\omega^2 C_1 C_2} \right)$$

Using $g_m = \beta/h_{11}$

$$R_{IN} = - \frac{g_m}{\omega^2 C_1 C_2}$$


Negative resistance

$$X_{IN} = \frac{1}{j\omega C_{IN}}$$

VCO – Resonance Frequency

$$C_{IN} = \frac{C_1 C_2}{C_1 + C_2}$$

Resonance frequency follows from condition:

$$X_{IN} = -X_{VARACTOR} \quad \text{where} \quad X_{VARACTOR} = j \left(\omega_0 L_3 - \frac{1}{\omega_0 C_3} \right)$$

which gives

$$-j \left(\omega_0 L_3 - \frac{1}{\omega_0 C_3} \right) - \frac{1}{j\omega_0} \left[\frac{1}{C_1} + \frac{1}{C_2} \right] = 0$$

and

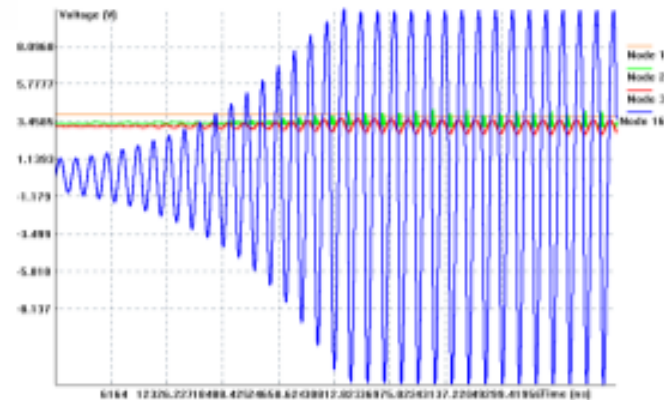
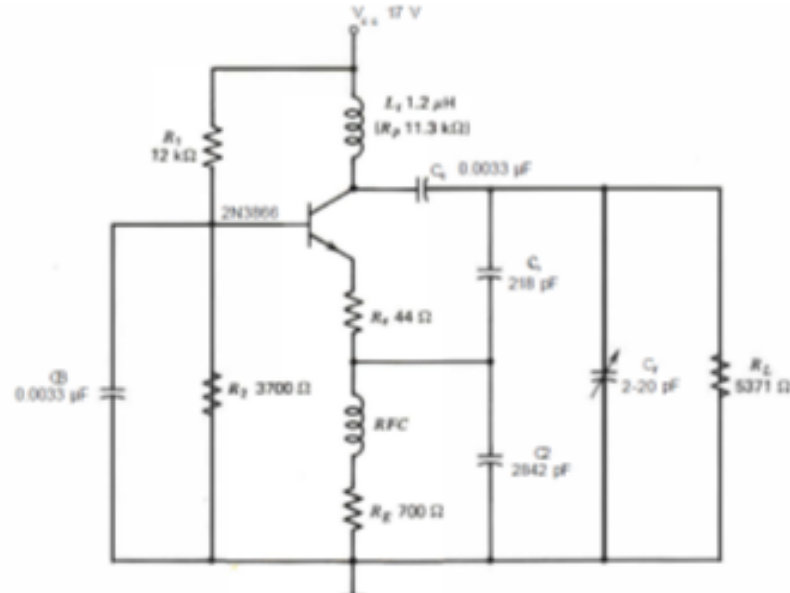
$$f_0 = \frac{1}{2\pi} \sqrt{\frac{1}{L_3} \left(\frac{1}{C_3} + \frac{1}{C_2} + \frac{1}{C_1} \right)}$$

Combined resistance of varactor diode must be equal to or less than $|R_{IN}|$ to create sustained oscillations

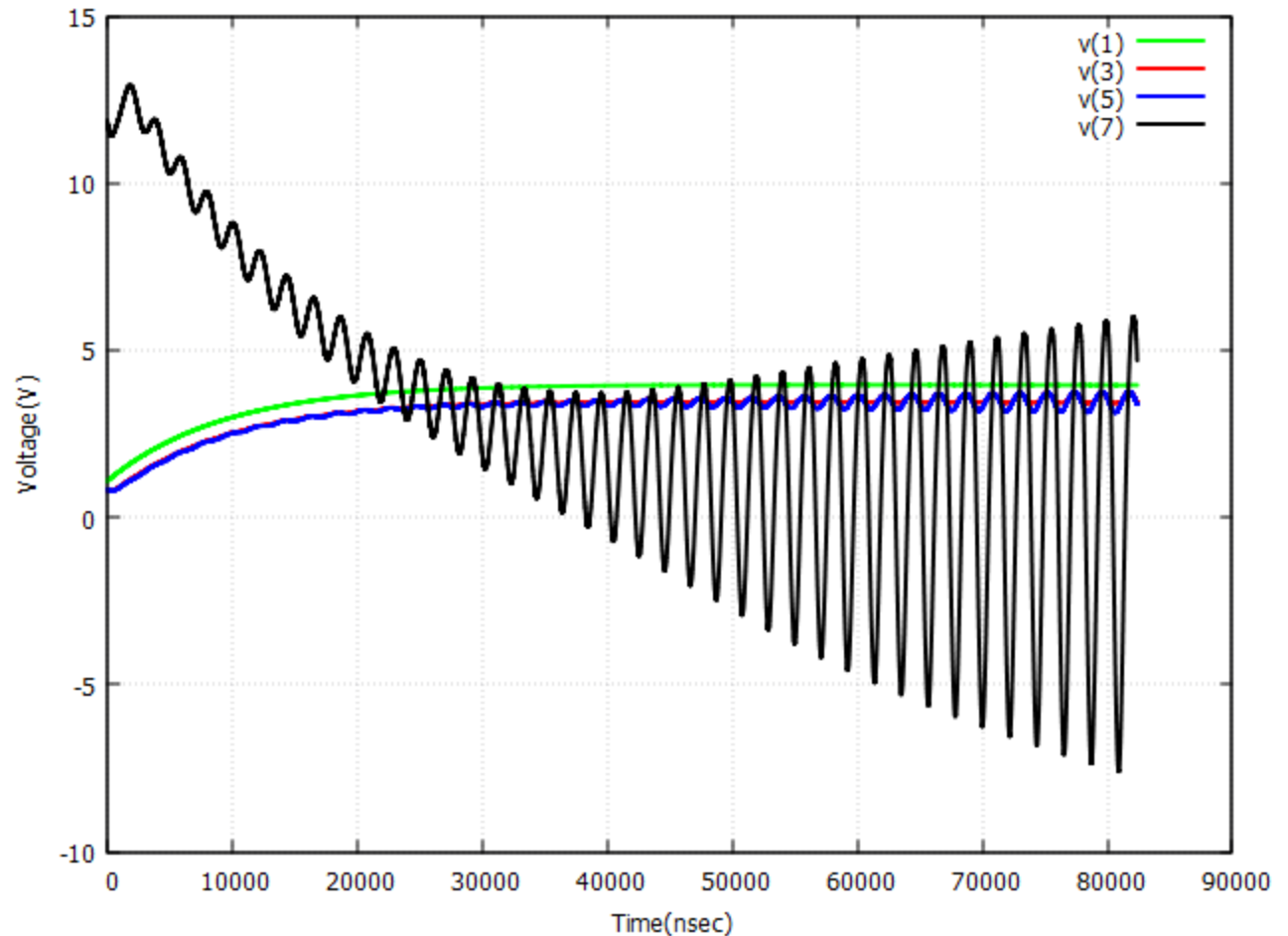
Simulation - Colpitts Oscillator

```

*BJT Circuit
q1 2 1 3 qmod
vcc 4 0 17.0
r1 4 1 12000
lt 4 2 1.2e-03
rp 4 2 11300
r2 1 0 3700
re 3 5 44.0
lrfc 5 6 100.8e-03
ree 6 0 700.0
cc 2 7 3.3e-09
c1 7 5 218.0e-12
c2 5 0 2.842e-09
cf 7 0 18.0e-12
rl 7 0 5371
cb 1 0 3.3e-09
*vin 5 0 pulse(0 8 0.1e-09 0.1e-09 0.1e-
09 0.1e-09 40.0e-09)
*vin 5 0 sin (0 8.0 10.0e+06 0.0 0.0 )
.tran 9.1490e-12 62000.4e-09
.print tran v(1) v(3) v(5) v(7)
.plot tran v(1) v(3) v(5) v(7)
.model qmod npn level=1 bf=100 vaf=50
is=8.0e-12 rb=100.0 cjc=0.5e-12
tf=0.06e-09
.LIM C=1.010e-12 L=0.1e-09 G=1.0e-20
P=5000 Q=200
.end
    
```



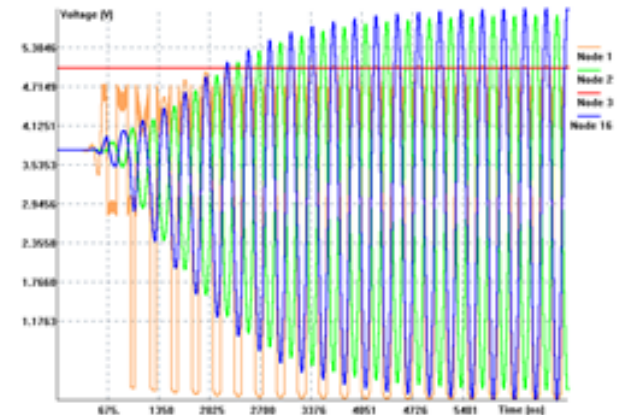
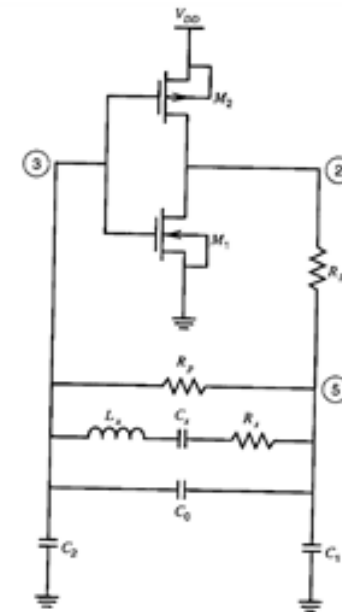
Simulation - Colpitts Oscillator



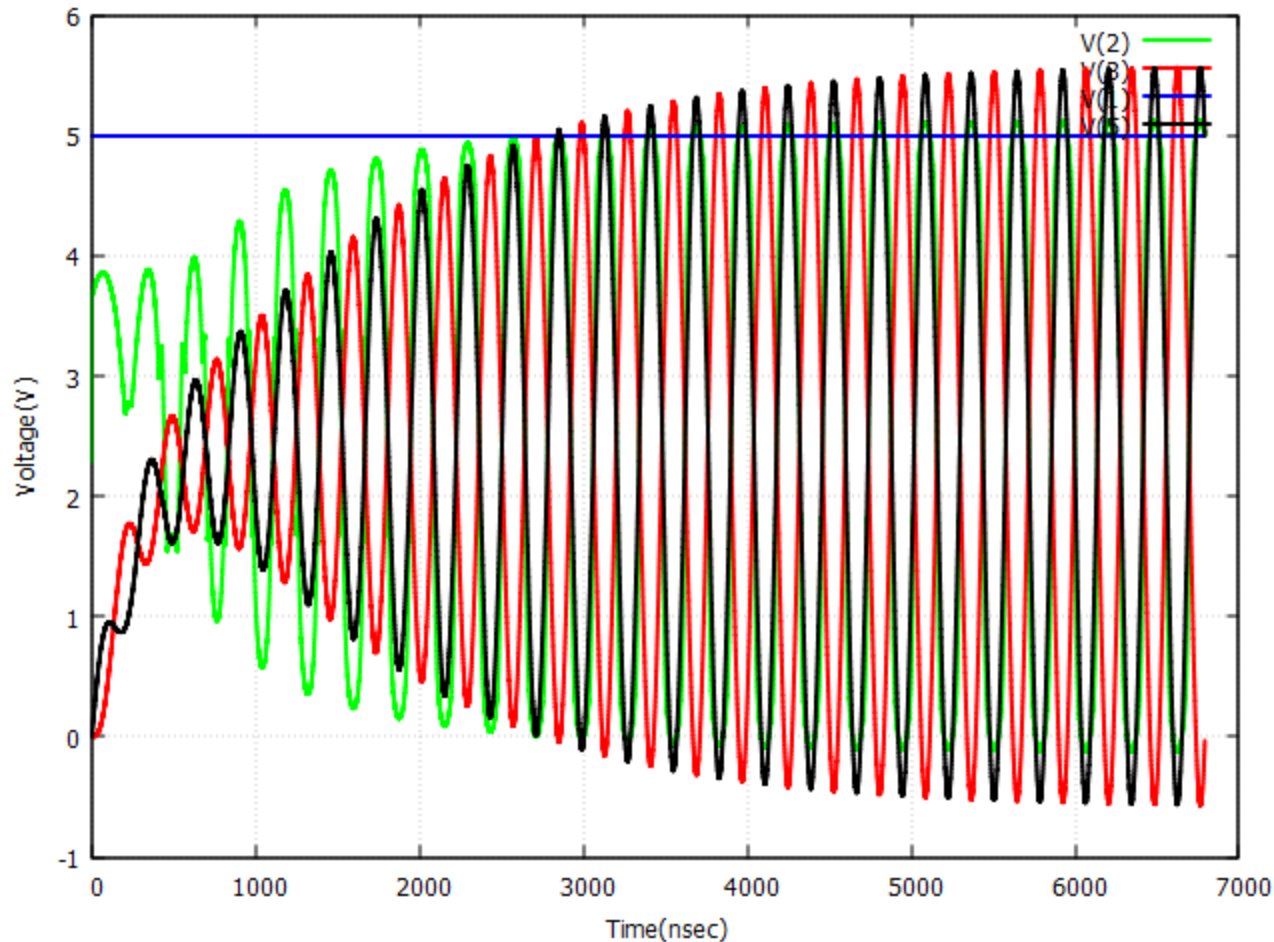
Simulation - Pierce Oscillator

```

*PIERCE XTAL OSCILLATOR WITH CMOS
M1 2 3 0 0 NMOS W=40U L=10U
M2 2 3 1 1 PMOS W=80U L=10U
RL 2 5 10000
C1 5 0 22.0e-12
C2 3 0 22.0e-12
RP 3 5 22.0e+06
LEFF 3 5 0.18e-03
VDD 1 0 5
.MODEL NMOS NMOS LEVEL=1 VTO=1 KP=20U
.LAMBDA=0.02
.MODEL PMOS PMOS LEVEL=1 VTO=-1 KP=10U
.LAMBDA=0.02
.tran 0.001e-09 6793.0e-09e-08
.LIM C=0.015e-12 L=0.1e-09 G=1.0e-20
.PRINT TRAN V(2) V(3) V(1) V(5)
.PLOT TRAN V(2) V(3) V(1) V(5)
.END
    
```



Simulation - Pierce Oscillator



Simulation - Ring Oscillator

```
*NMOS RING OSCILLATOR SPICEBOOK PAGE 183
VDD 11 0 5
M1 1 3 0 0 ENH L=10U W=40U
M2 2 1 0 0 ENH L=10U W=40U
M3 3 2 0 0 ENH L=10U W=40U
M4 11 1 1 0 DEP L=10U W=5U
M5 11 2 2 0 DEP L=10U W=5U
M6 11 3 3 0 DEP L=10U W=5U
*VIN 1 0 PULSE (0 5.0 0.2e-09 .5e-09
.5e-09 1.0e-09 6.0e-06)
*VAN 2 0 PULSE (4.86 0.0 0.2e-09 .5e-09
.5e-09 1.0e-09 6.0e-06)
.TRAI .15e-09 888.0e-09
.MODEL DEP NMOS LEVEL=1 VTO=-3 LAMBDA=.001
KP=.4E-4
.MODEL ENH NMOS LEVEL=1 VTO=1.8 CGSO=20H
LAMBDA=.001 KP=.4E-4
.PRINT TRAI V(1) V(2) V(3) V(11)
.PLOT TRAI V(1) V(2) V(3) V(11)
.LIM C=10.0e-12 L=0.01e-09 P=20 O=10 D=0
.END
```

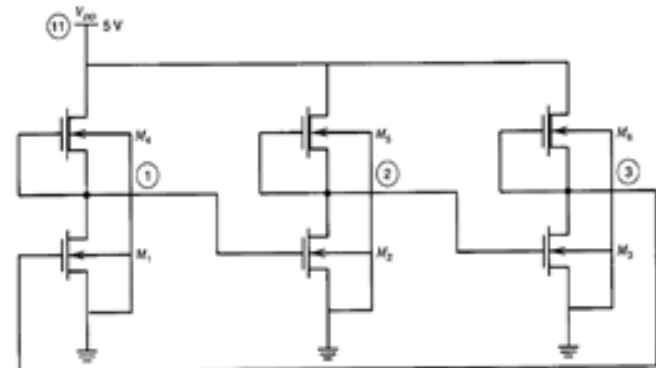


Figure 6.9 NMOS ring oscillator.

